

## SILICON EPITAXIAL SWITCHING DIODE

1N4148W



SOD-123  
PLASTIC PACKAGE

1N4148W= A2 with cathode band

Fast Switching Diode

### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ )

DESCRIPTION	SYMBOL	VALUE	UNIT
Continuous Reverse Voltage	$V_R$	75	V
Repetitive Peak Reverse Voltage	$V_{RRM}$	100	V
Average rectified Current half wave rectification with resistive load $f \geq 50$ Hz	$*I_F (AV)$	150	mA
Surge Forward Current $t < 1$ s and $T_j=25^\circ\text{C}$	$I_{FSM}$	500	mA
Power Dissipation	$*P_{tot}$	400	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to +150	$^\circ\text{C}$

### THERMAL RESISTANCE

Junction to Ambient in free air	$*R_{th (j-a)}$	450	$^\circ\text{C/W}$
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\*Valid provided that electrodes are kept at ambient Temperature

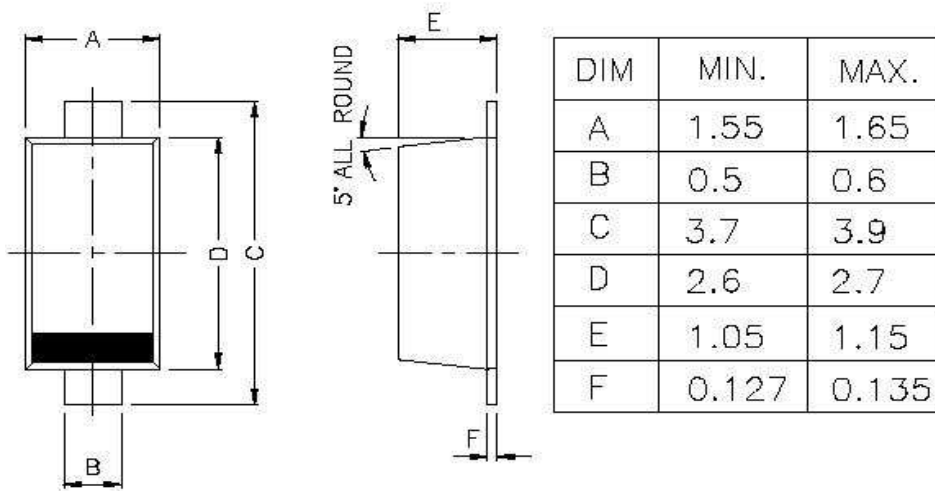
### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$ unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Forward Voltage	$V_F$	$I_F=10\text{mA}$		1.0	V
Reverse Current	$I_R$	$V_R=20\text{V}$		25	nA
		$V_R=20\text{V}, T_j=150^\circ\text{C}$		50	$\mu\text{A}$
		$V_R=75\text{V}$		5.0	$\mu\text{A}$

### DYNAMIC CHARACTERISTICS

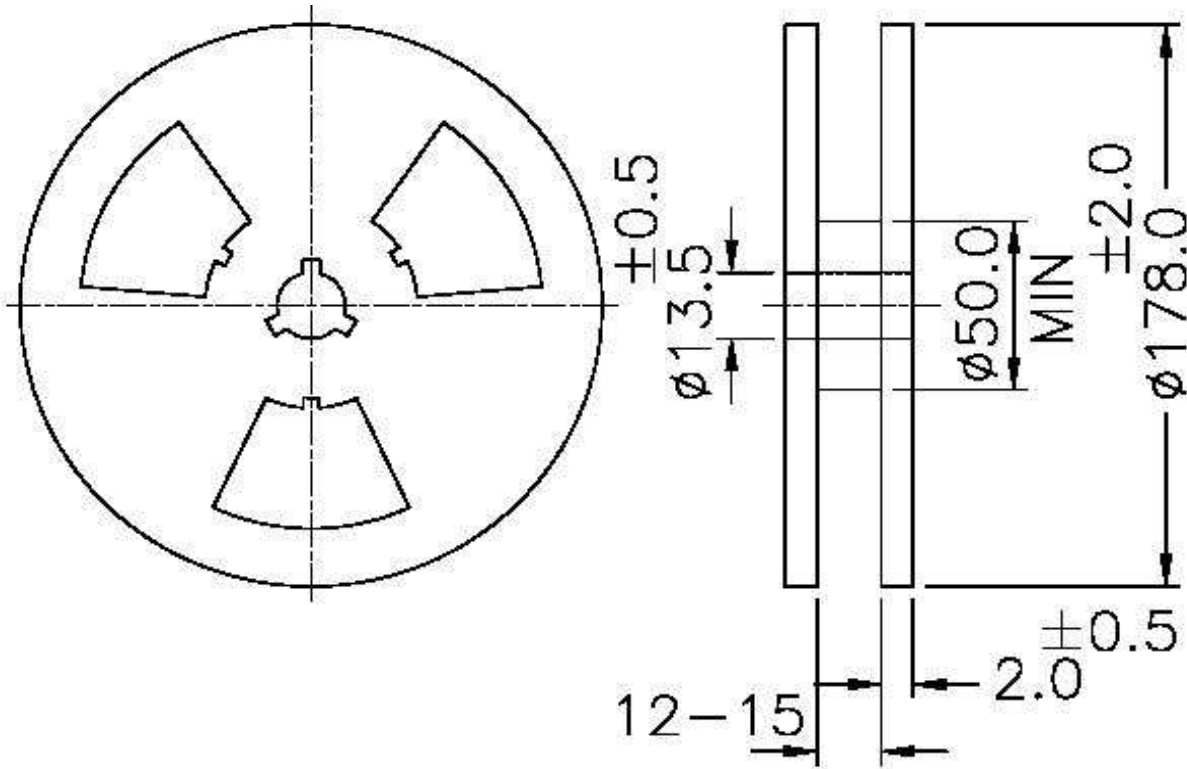
Diode Capacitance	$C_d$	$V_R=0\text{V}, f=1\text{MHz}$		4.0	pF
Voltage Rise When Switching On (tested with 50ms pulses)	$V_{fr}$	tested with=50mA pulses, $t_p=0.1\mu\text{s}$ , rise time= $\leq 30$ ns, $t_p= (5$ to 100) KHz		2.5	ns
Reverse Recovery Time	$t_{rr}$	$I_F=10\text{mA}$ , to $I_R=1\text{mA}$ , $R_L=100\ \Omega$ , at $V_R=6\text{V}$		4.0	ns
Rectification Efficiency	$\eta_v$	$f=100\text{MHz}, V_{RF}=2\text{V}$	0.45		

1N4148W Rev020905E

PACKAGE SOD-123 FL

All dimensions are in mm

CATHODE IS MARKED BY BAND



ALL DIMENSIONS ARE IN mm  
 REEL  $\varnothing$  178 mm (7")  
 3000 Pcs / REEL

#### Component Disposal Instructions

1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

### **Disclaimer**

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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